# Nb/Cu thin film HiPIMS coatings optimization for SRF applications

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 $E_{acc} = 10 \text{ MV/m}$ 

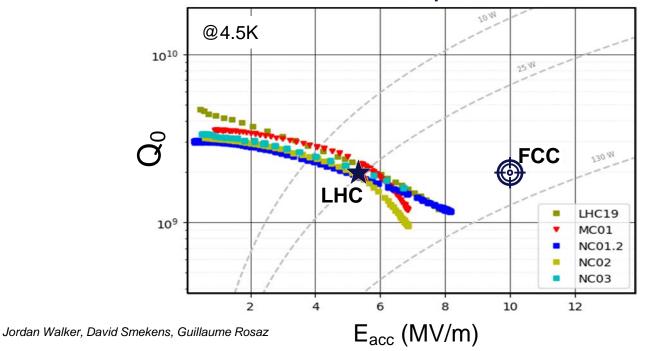
 $Q_0$  above  $2x10^9$ 

@4.5 K

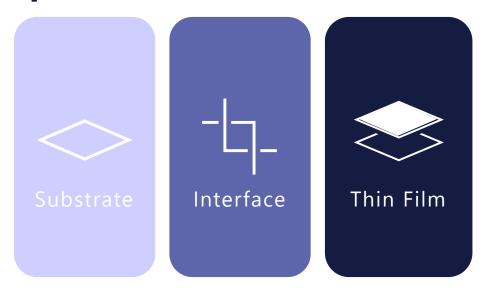
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### **MOTIVATION**

#### 400MHz LHC cavities spares: last results



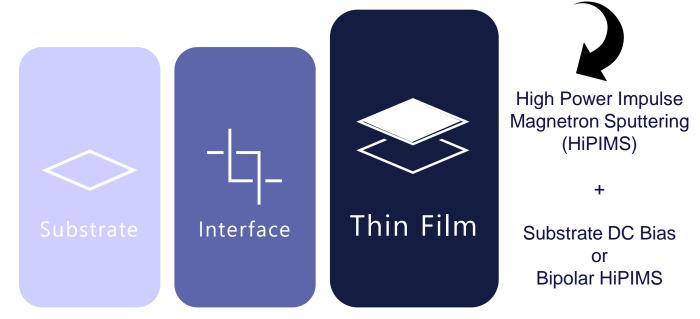
### R&D axis of research at CERN to improve the performance of SRF cavities



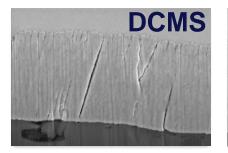
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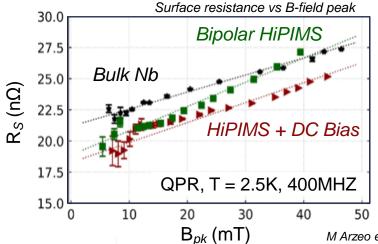


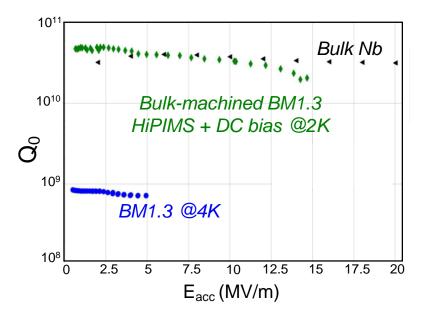


### Why HiPIMS?

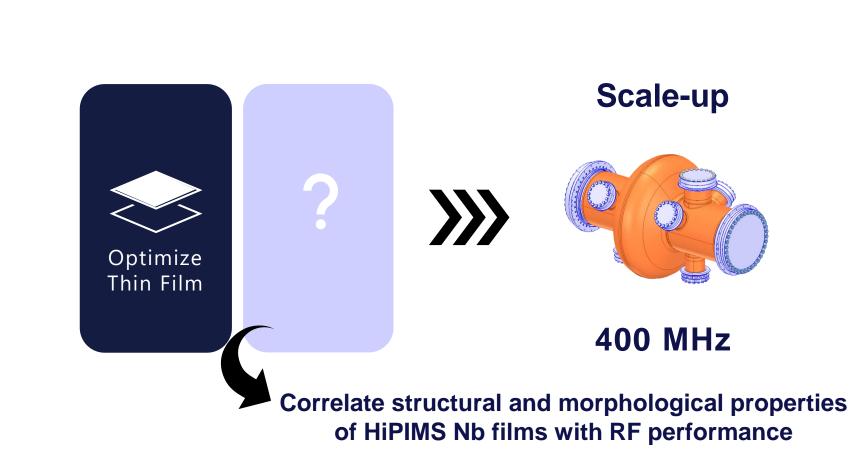






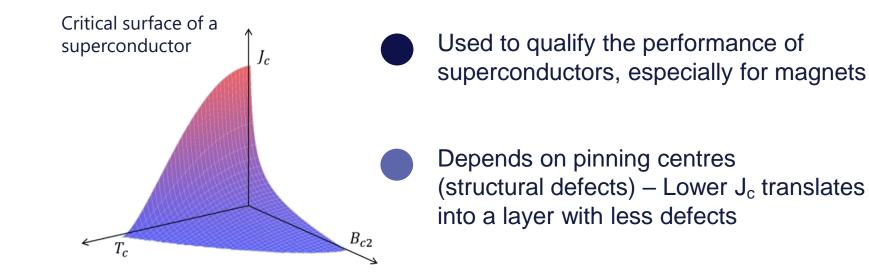


M Arzeo et al 2022 Supercond. Sci. Technol. 35 054008



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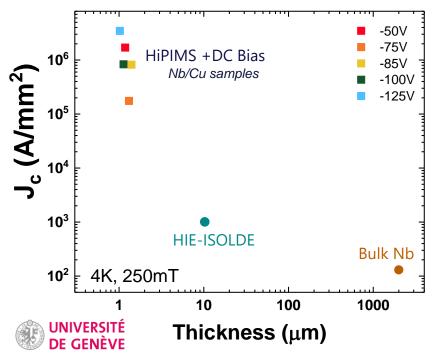
### **CRITICAL CURRENT DENSITY J**<sub>C</sub>



FCO

## **CRITICAL CURRENT DENSITY J**<sub>C</sub>

#### Where are we?

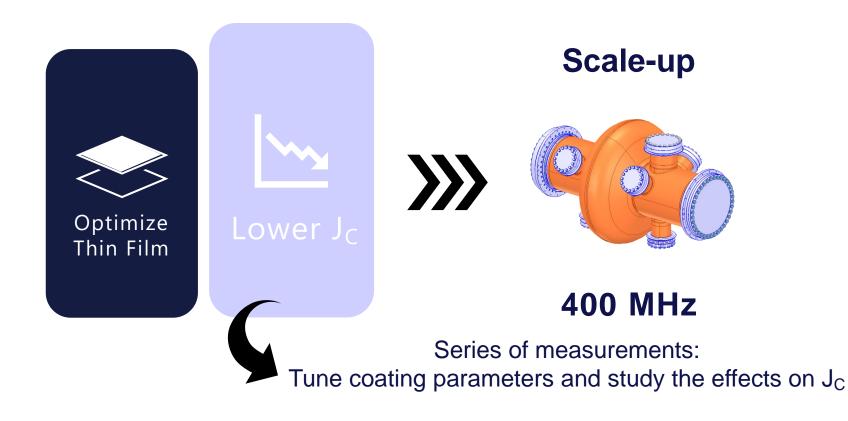


J<sub>C</sub> of our HiPIMS samples is orders of magnitude higher than HIE-ISOLDE ( $E_{acc}$  up to 120mT, corresponding to ~30MV/m in an elliptical cavity) and Bulk Nb ( $E_{acc}$  up to 49 MV/m with Q<sub>0</sub>>10<sup>10</sup>)

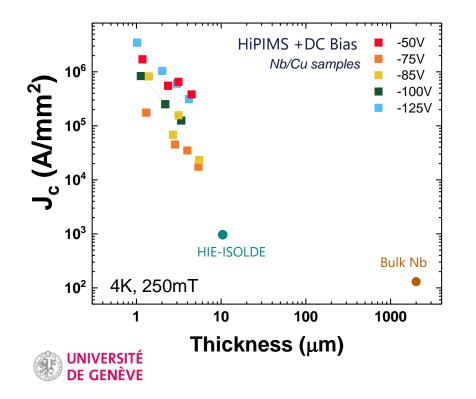
Lower J<sub>C</sub> seems to result in better RF performance

There's room for improvement in our films





## THICKNESS vs J<sub>C</sub>



J<sub>C</sub> decreases with increasing film thickness Independently of bias

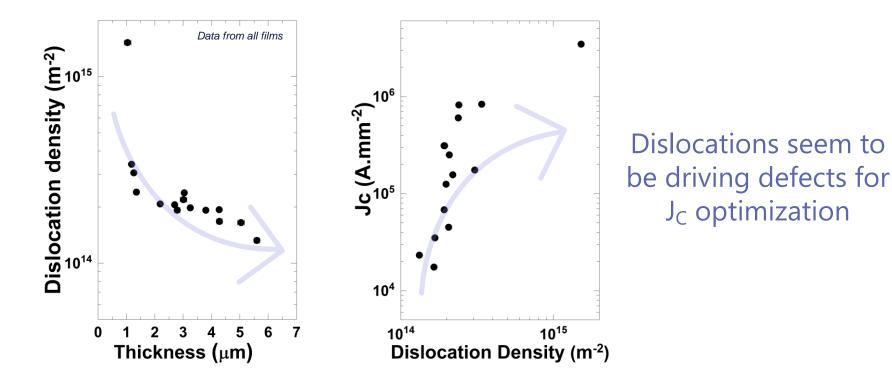
# What morphological property is responsible for this?

i. e. which defect family disappears gradually with increasing thickness?

10

J<sub>C</sub> optimization

### **DISLOCATION DENSITY vs J**<sub>C</sub>

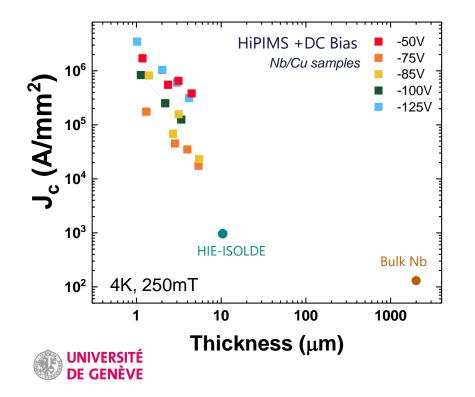


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### ION BOMBARDMENT ENERGY vs J<sub>C</sub>



Bias voltage applied corresponds to the ion energy impinging the surface

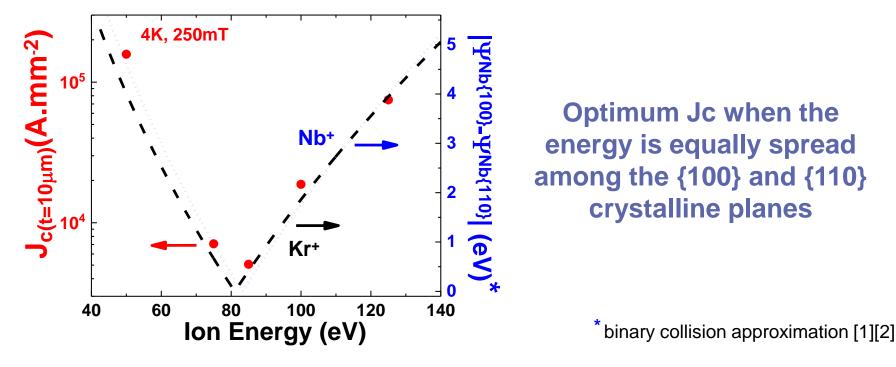
 $E_{ion} = |eV_B|$ 

**Nonlinear relation:** 

optimum J<sub>C</sub> with -80V applied DC bias

### ION BOMBARDMENT ENERGY vs J<sub>C</sub>

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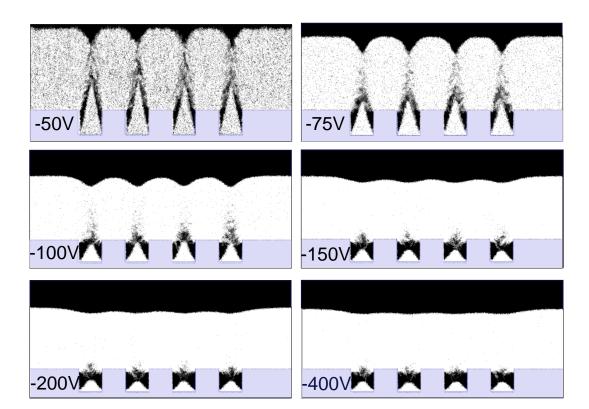
[1] D. K. Brrce et al. Nuclear Instruments and Methods in Physics Research, 44 1989 68-78 [2] Z.Q. Ma et al. Applied Surface Science 137 1999 184–190M



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Can we planarize a layer deposited on a very rough substrate with HiPIMS?



# Planarization vs substrate DC bias

#### **NASCAM** simulations

Textured Si substrate No surface diffusion (thermal effects neglected) 100% ionized Nb Impinging angle:  $(90\pm10)^{\circ}$ 

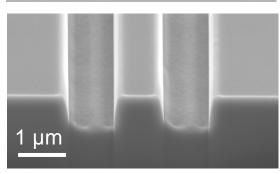
HiPIMS + substrate DC bias

### **Nb PLANARIZATION**

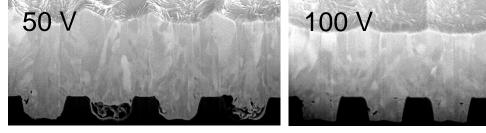
### FIB milling

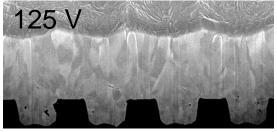


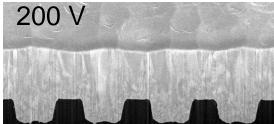
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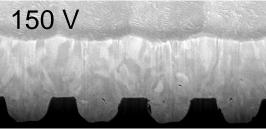


Si samples w/ 1x1x20 µm trenches









1 µm





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# FUTURE WORK

Post coating annealing Coating temperature

JC

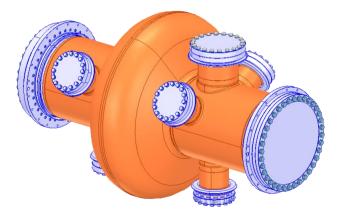
Substrate treatment



### **Nb** planarization

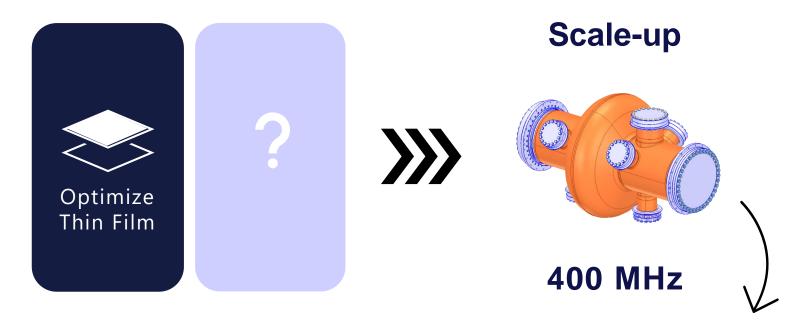
Coating Cu cavity first with a very thin Nb layer at high bias and then coat rest of the layer with optimal HiPIMS recipe

### **Scale-up HiPIMS**



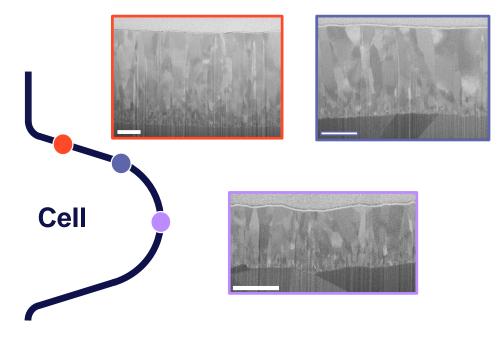
### **400 MHz cavities**



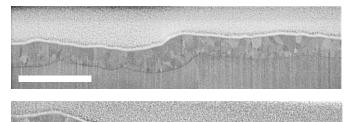


HiPIMS + substrate DC bias not yet possible Bipolar HiPIMS compatible with current setup

### **400 MHz ACTIVITIES**



### BIPOLAR HiPIMS (+80V) coating trial on samples





**HOM ports** 

and the processing of

) fC<u>C</u>

### **400 MHz ACTIVITIES**

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### 1<sup>st</sup> BIPOLAR HiPIMS cavity coating on 05/2022

RF performance to be measured June/July 2022



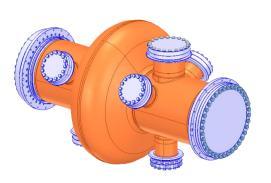
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### FUTURE WORK

### **BIPOLAR HIPIMS**

RF performance of 1<sup>ST</sup> test cavity to be measured

Optimize coating setup and parameters



### HiPIMS + DC bias

- Proven on 1.3GHz Lot of RF data
- More complex coating setup Upgraded cathode under study Grid like anode needed + cavity
  - insulation



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## Thank you for your attention!